

Abstract Submitted  
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**Josephson and Multi-Gap Quasi-Particle Tunneling in Crystalline MgB<sub>2</sub>-based Junctions with an MgO Sputtered Barrier**<sup>1</sup> JEAN-BAPTISTE LALOE, MIT, J. S. MOODERA, SCTF TEAM — MgB<sub>2</sub> is a multi-gap superconductor with a T<sub>C</sub> of 39K and a hexagonal structure. This simple and stable compound is very attractive for device applications. We have deposited and patterned micron-sized SIS tunnel junctions with highly textured MgB<sub>2</sub> electrodes grown by MBE co-evaporation with sputter-deposited MgO tunnel barriers, in an entirely in-situ process. This method enabled us to obtain low resistance junctions with very good oxide coverage. We present  $I - V$  and  $dI/dV$  data displaying Josephson pair tunneling as well as the quasi-particle tunneling signature of both the Pi- and Sigma-bands of the MgB<sub>2</sub>. Our experimental gap values agree with theoretical calculations. Although our MgB<sub>2</sub> films were  $c$ -axis oriented, growth-related roughness of the bottom MgB<sub>2</sub> enable  $a/b$ -axis tunneling and thus explain the observed Sigma-band features. We link our data to a simple model assuming tunneling to occur from both the Pi- and Sigma-bands in parallel, proportionally weighted depending on the interfacial topography.

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